32V PNP POWER SWITCHING TRANSISTOR IN SOT89

Features

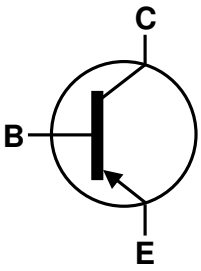
- BV_{CEO} > -32V
- I_C = -1A High Continuous Collector Current
- Complementary NPN Type: 2DD1664
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

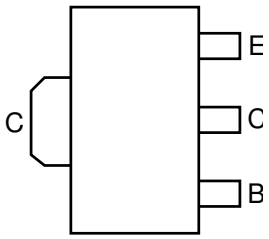
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.055 grams (Approximate)

SOT89

Top View



Device Symbol



Pin Out
Top View

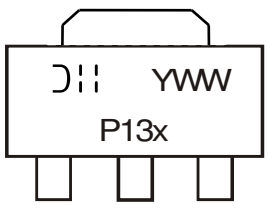
Ordering Information (Note 4)

Part Number	Status	Marking Code	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DB1132P-13	Obsolete	P13P	13	12	2,500
2DB1132Q-13	Obsolete	P13Q	13	12	2,500
2DB1132R-13	Active	P13R	13	12	2,500
2DB1132R-13R	Active	P13R	13	12	4,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

(Top View)



= Manufacturer's Marking
P13x = Product Type Marking Code:
Where P13P = 2DB1132P
P13Q = 2DB1132Q
P13R = 2DB1132R
YWW = Date Code Marking
Y = Last Digit of Year (ex: 1 = 2021)
WW = Week Code (01 to 52)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-1	A
Peak Pulse Current	I_{CM}	-2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

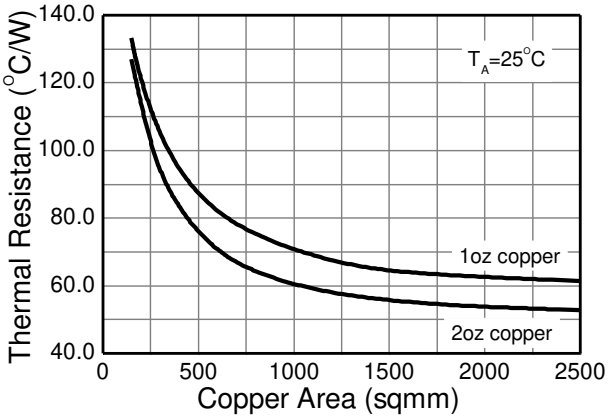
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	1	W
	(Note 6)		1.5	
	(Note 7)		2	
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	125	°C/W
	(Note 6)		83	
	(Note 7)		60	
Thermal Resistance, Junction to Case	(Note 5)	$R_{\theta JC}$	18	°C/W
Thermal Resistance, Junction to Lead	(Note 8)	$R_{\theta JL}$	22	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

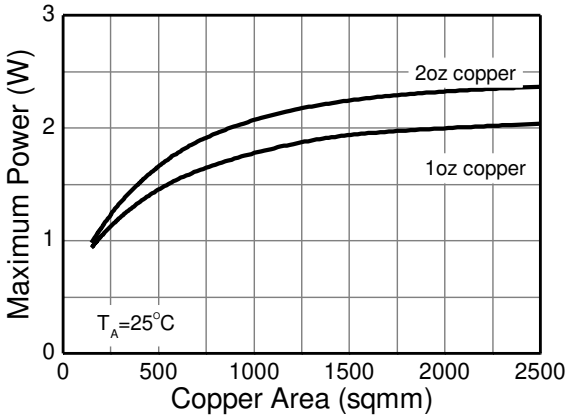
ESD Ratings (Note 9)

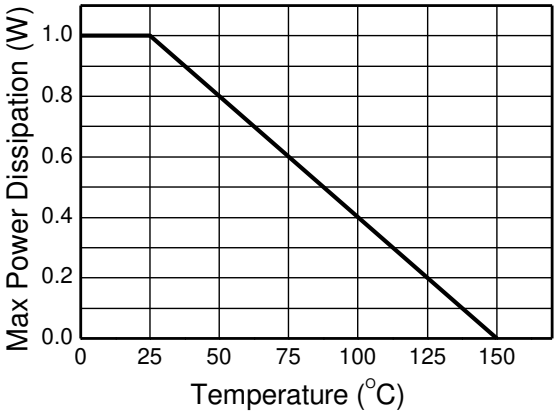
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
8. Thermal resistance from junction to solder-point (on the exposed collector pad).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

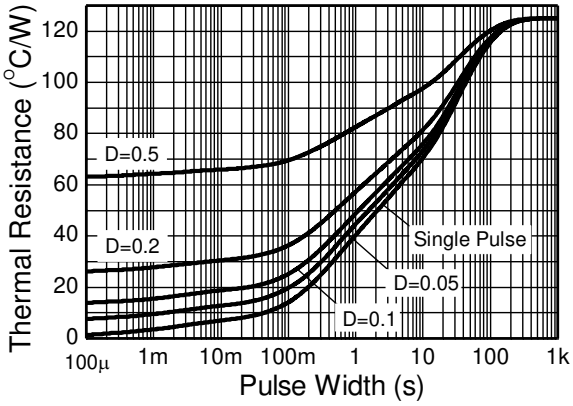
Thermal Characteristics and Derating Information



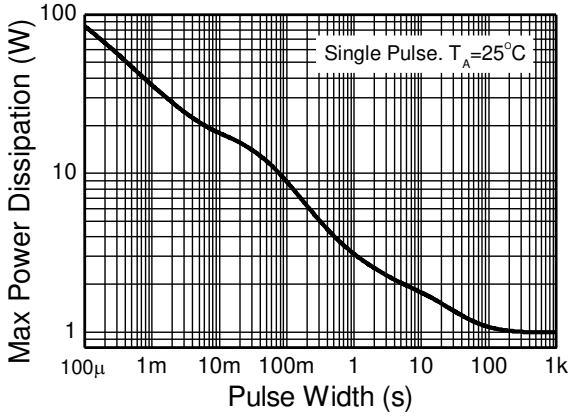




Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_{CBO}	-40	—	—	V	I_C = -50μA
Collector-Emitter Breakdown Voltage (Note 10)		BV_{CEO}	-32	—	—	V	I_C = -1mA
Emitter-Base Breakdown Voltage		BV_{EBO}	-5	—	—	V	I_E = -50μA
Collector Cut-Off Current		I_{CBO}	—	—	-0.5	μA	V_{CB} = -20V
Emitter Cut-Off Current		I_{EBO}	—	—	-0.5	μA	V_{EB} = -4V
Static Forward Current Transfer Ratio (Note 10)	2DB1132P	h_{FE}	82	—	180	—	I_C = -100mA, V_{CE} = -3V
	2DB1132Q		120		270		
	2DB1132R		180		390		
Collector-Emitter Saturation Voltage (Note 10)		$V_{CE(sat)}$	—	-125	-500	mV	I_C =-500mA, I_B = -50mA
Transition Frequency		f_T	—	190	—	MHz	I_E = -50mA, V_{CE} = -5V, f = 30MHz
Output Capacitance		C_{obo}	—	12	30	pF	I_E = 0A, V_{CB} = -10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

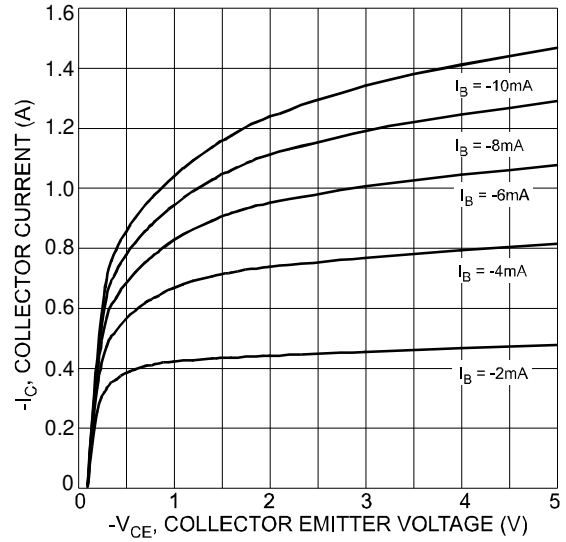


Fig. 1 Typical Collector Current vs. Collector-Emitter Voltage

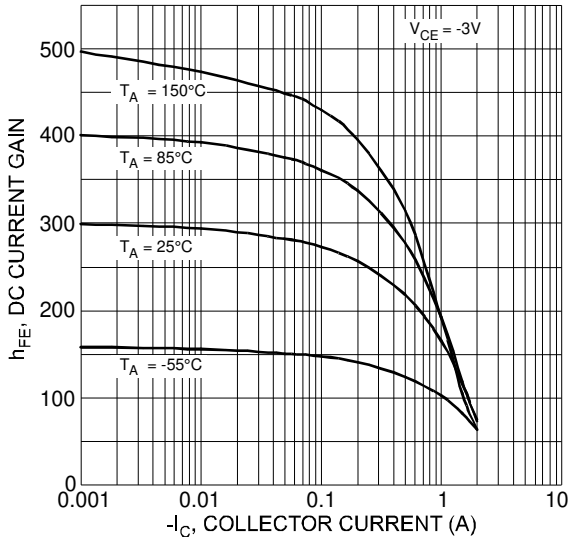


Fig. 2 Typical DC Current Gain vs. Collector Current (2DB1132R)

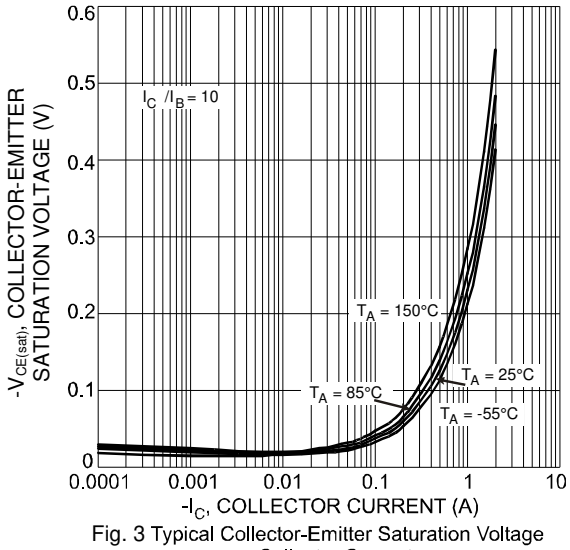


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

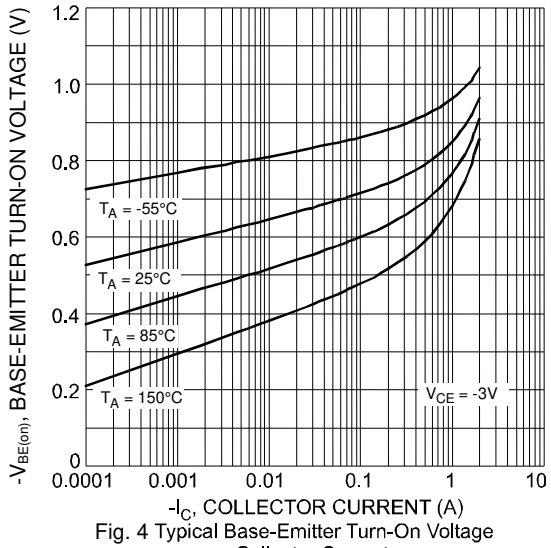


Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

Typical Electrical Characteristics (continued) (@T_A = +25°C, unless otherwise specified.)

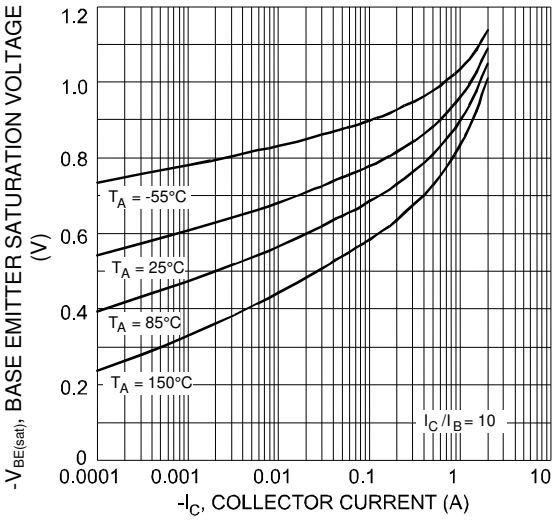


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

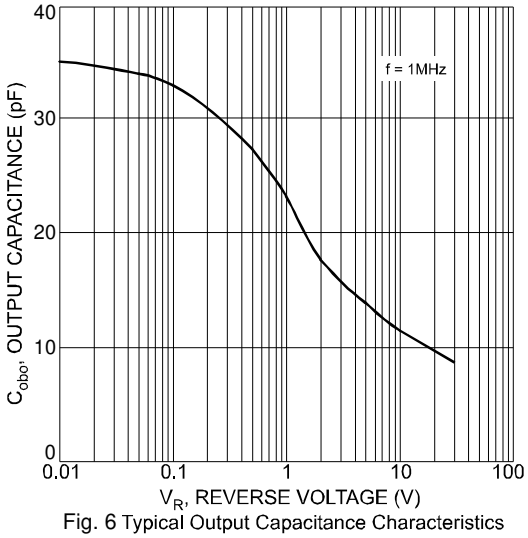


Fig. 6 Typical Output Capacitance Characteristics

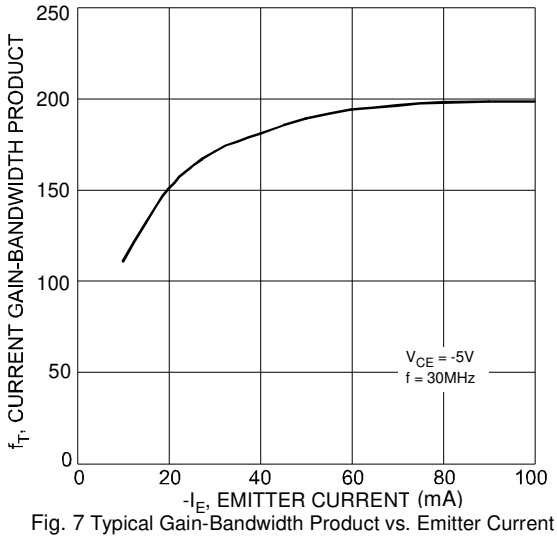
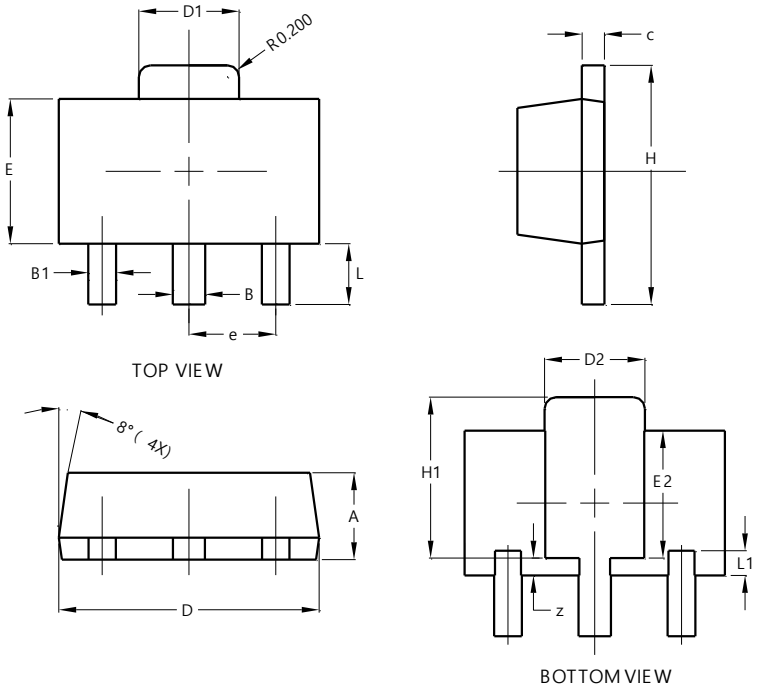


Fig. 7 Typical Gain-Bandwidth Product vs. Emitter Current

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

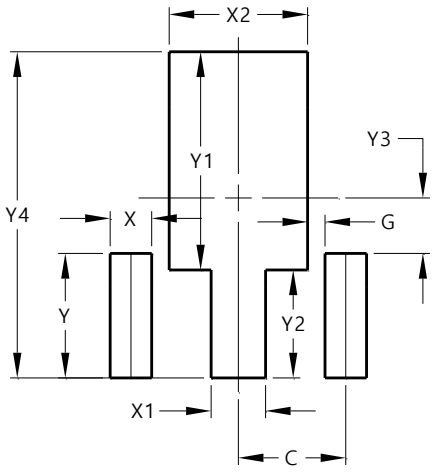


SOT89			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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